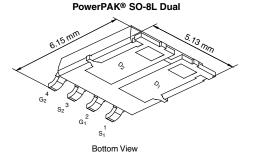
SQJ910EP



Vishay Siliconix

Automotive Dual N-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	30				
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.0110				
$R_{DS(on)}$ (Ω) at V_{GS} = 4.5 V	0.0120				
I _D (A) per leg	8				
Configuration	Dual				

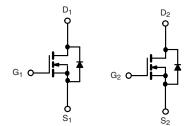


FEATURES

- TrenchFET[®] Power MOSFET
- 100 % R_g and UIS Tested
- AEC-Q101 Qualified^d
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>



RoHS COMPLIANT HALOGEN FREE



N-Channel MOSFET N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and Halogen-free	SQJ910EP-T1-GE3

ABSOLUTE MAXIMUM RATINGS	S (T _C = 25 °C, unless	s otherwise noted	ł)		
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V _{DS}	30	N/	
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current ^a	T _C = 25 °C	I	8		
Continuous Drain Currenta	T _C = 125 °C	ID	8		
Continuous Source Current (Diode Conduction) ^a		I _S	8	А	
Pulsed Drain Current ^b		I _{DM}	32		
Single Pulse Avalanche Current		I _{AS}	33		
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	55	mJ	
Maximum Bower Dissinction ^b	T _C = 25 °C	D	48	W	
Maximum Power Dissipation ^b	T _C = 125 °C	PD	16	vv	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C	
Soldering Recommendations (Peak Temperature) ^{e, f}			260		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	85	°C/W
Junction-to-Case (Drain)		R _{thJC}	3.1	C/W

Notes

- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.
- e. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

a. Package limited.

SQJ910EP

SPECIFICATIONS ($T_C = 25 \ ^{\circ}C$,	1	1						
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static				30		-	1	
Drain-Source Breakdown Voltage	V _{DS}	55	$V_{GS} = 0 V, I_D = 250 \mu A$		-	-	v	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μΑ	1.3	1.8	2.3		
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 30 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = 30 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA	
		$V_{GS} = 0 V$	V_{DS} = 30 V, T_J = 175 °C	-	-	150		
On-State Drain Current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	30	-	-	Α	
		$V_{GS} = 10 V$	I _D = 9.8 A	-	0.0092	0.0110	Ω	
Drain-Source On-State Resistance ^a	В	$V_{GS} = 4.5 V$	I _D = 9.4 A	-	0.0100	0.0120		
Drain-Source On-State Resistance	R _{DS(on)}	$V_{GS} = 10 V$	I _D = 9.8 A, T _J = 125 °C	-	-	0.0160		
		V _{GS} = 10 V	I _D = 9.8 A, T _J = 175 °C	-	-	0.0190		
Forward Transconductanceb	9 _{fs}	V _{DS}	= 15 V, I _D = 9.8 A	-	46	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}		V _{DS} = 15 V, f = 1 MHz	-	1797	2245	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	375	469		
Reverse Transfer Capacitance	C _{rss}			-	154	193		
Total Gate Charge ^c	Qg			-	32.7	49		
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	V _{DS} = 15 V, I _D = 11.3 A	-	5.2	-	nC	
Gate-Drain Charge ^c	Q _{gd}			-	5	-	1	
Gate Resistance	R _g	f = 1 MHz		1.8	3.74	5.6	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	10	15		
Rise Time ^c	t _r	$\label{eq:V_DD} \begin{array}{l} V_{\text{DD}} = 15 \; V, \; R_{\text{L}} = 1.4 \; \Omega \\ I_{\text{D}} \cong 11 \; A, \; V_{\text{GEN}} = 10 \; V, \; R_{\text{g}} = 1 \; \Omega \end{array}$		-	10	15	- ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	26	39		
Fall Time ^c	t _f			_	9	13		
Source-Drain Diode Ratings and Char	acteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	32	Α	
Forward Voltage	V _{SD}	c =	6.8 A, V _{GS} = 0 V	_	0.8	1.1	V	

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$

b. Guaranteed by design, not subject to production testing.

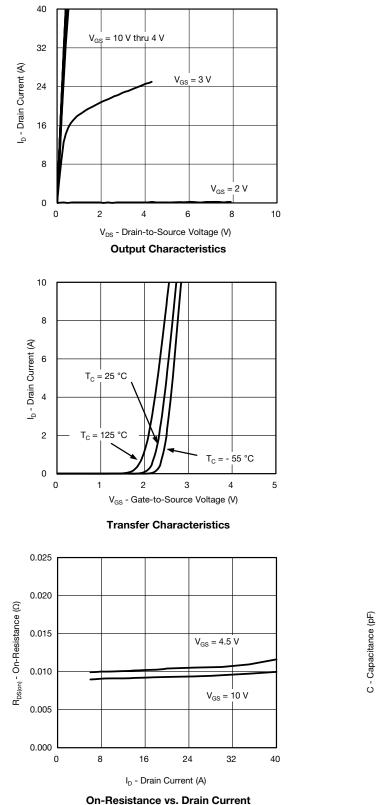
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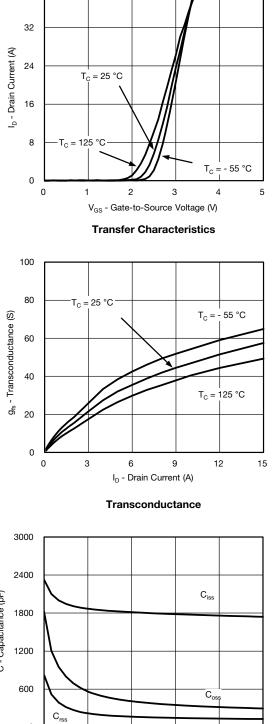
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)





40

S13-1398-Rev. B, 24-Jun-13

0

0

6

12

18

V_{DS} - Drain-to-Source Voltage (V)

Capacitance

24

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30

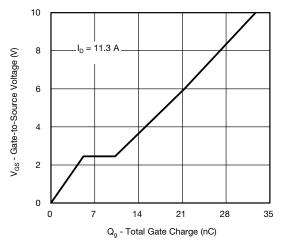
For technical questions, contact: <u>automostechsupport@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



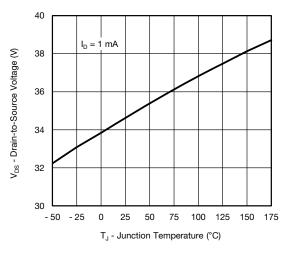
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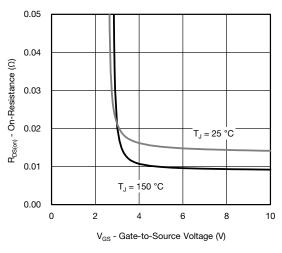
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



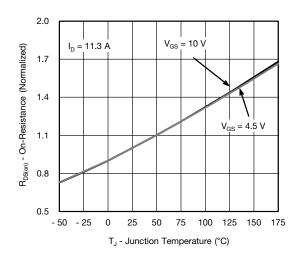




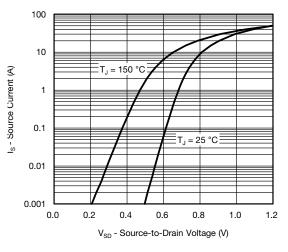
Drain-Source Breakdown vs. Junction Temperature



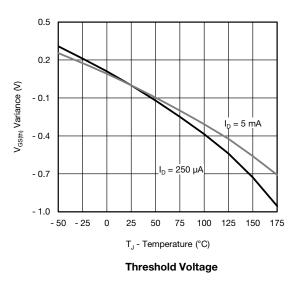
On-Resistance vs. Gate-to-Source Voltage



On-Resistance vs. Junction Temperature



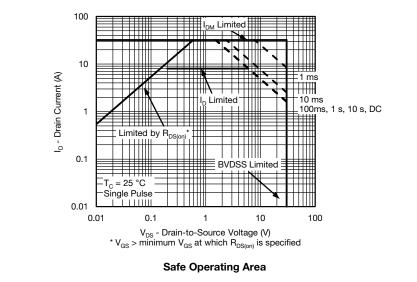
Source Drain Diode Forward Voltage

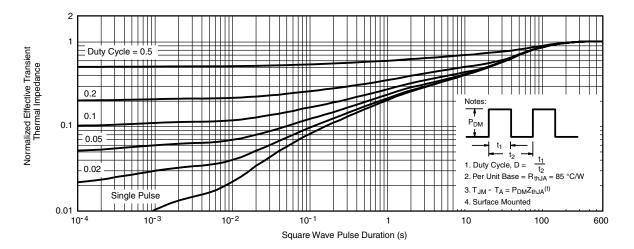


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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)





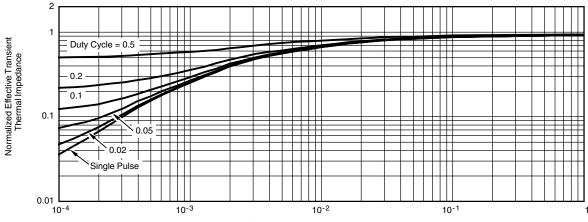
Normalized Thermal Transient Impedance, Junction-to-Ambient



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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Square Wave Pulse Duration (s)

Normalized Thermal Transient Impedance, Junction-to-Case

Note

· The characteristics shown in the two graphs

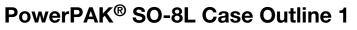
- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62810.

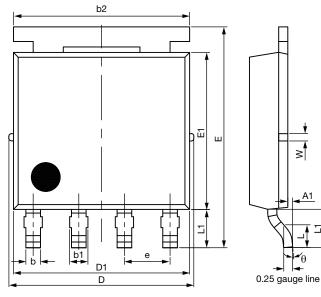


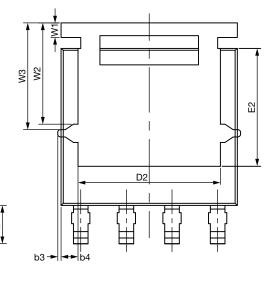


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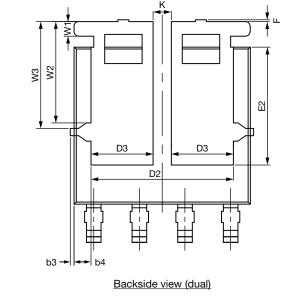
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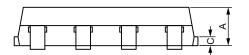




Topside view

Backside view (single)





Package Information



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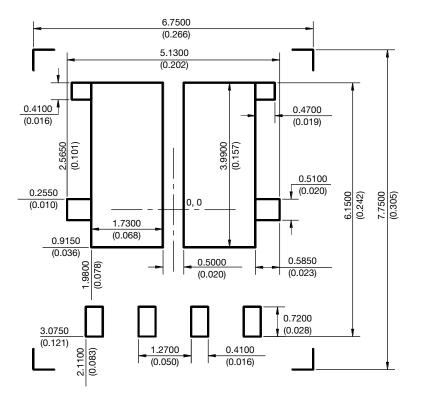
DIM	MILLIMETERS			INCHES			
DIM.	MIN. NOM. MAX.			MIN. NOM. MAX.			
А	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094			0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC		0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	3.18	3.28	3.38	0.125	0.129	0.133	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
К		0.51			0.020		
W		0.23		0.009			
W1	0.41		0.016				
W2	2.82		0.111				
W3		2.96		0.117			
θ	0°	-	10°	0°	-	10°	

Note

• Millimeters will gover



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L DUAL



Recommended Minimum Pads Dimensions in mm (inches) Keep-out 6.75 (0.266) x 7.75 (0.305)

Revision: 07-Feb-12



Vishay

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